# APR 0 7 2008

### Rorm 1449 (Modified)

# Information Disclosure Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No.	NOVLP097/NVLS-2906	
Application No.:	10/807,680	
Applicant	Wu et al.	
Filing Date	March 23, 2004	
Group	1792	
	Page 1 of 4	

### **U.S. Patent Documents**

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Initial			Date	Patent Office		Class	Yes No
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Examiner /Marianne Padgett/	Date Considered	07/03/2008

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	NOVLP097/NVLS-2906
	Application No.:	10/807,680
Information Disclosure	Applicant	Wu et al.
Statement By Applicant	Filing Date	March 23, 2004
	Group	1792
(Use Several Sheets if Necessary)		Page 2 of 4

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Examiner	/Marianne Padgett/	Date Considered	07/03/2008
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	NOVLP097/NVLS-2906
	Application No.:	10/807,680
<b>Information Disclosure</b>	Applicant	Wu et al.
Statement By Applicant	Filing Date	March 23, 2004
	Group	1792
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/Marianne Padgett/ Date Sousidered 07/03/2008	Examiner	/Marianne Padgett/	Date Considered	07/03/2008
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	NOVLP097/NVLS-2906
	Application No.:	10/807,680
Information Disclosure	Applicant	Wu et al.
Statement By Applicant	Filing Date	March 23, 2004
	Group	1792
(Use Several Sheets if Necessary)		Page 4 of 4

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	Examiner	/Marianne Padgett/	Date Considered	07/03/2008	
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